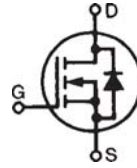


**Depletion Mode
MOSFET**
**IXTH16N10D2
IXTT16N10D2**

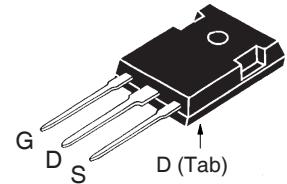
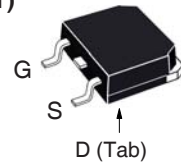
$$V_{DSX} = 100V$$

$$I_{D(on)} \geq 16A$$

$$R_{DS(on)} \leq 64m\Omega$$

N-Channel


Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	$T_J = 25^\circ C$ to $150^\circ C$	100	V
V_{DGX}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$	100	V
V_{GSX}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
P_D	$T_C = 25^\circ C$	695	W
T_J		- 55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		- 55 ... +150	$^\circ C$
T_L	1.6mm (0.062 in.) from Case for 10s	300	$^\circ C$
T_{SOLD}	Plastic Body for 10s	260	$^\circ C$
M_d	Mounting Torque (TO-247)	1.13 / 10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

TO-247 (IXTH)

TO-268 (IXTT)


G = Gate D = Drain
S = Source Tab = Drain

Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSX}	$V_{GS} = -5V$, $I_D = 250\mu A$	100		V
$V_{GS(off)}$	$V_{DS} = 25V$, $I_D = 1mA$	- 2.0		V
I_{GSX}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
$I_{DSX(off)}$	$V_{DS} = V_{DSX}$, $V_{GS} = -5V$ $T_J = 125^\circ C$			5 μA 75 μA
$R_{DS(on)}$	$V_{GS} = 0V$, $I_D = 8A$, Note 1			64 m Ω
$I_{D(on)}$	$V_{GS} = 0V$, $V_{DS} = 25V$, Note 1	16		A

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}, I_D = 8\text{A}$, Note 1	7	11	S
C_{iss}	$V_{GS} = -10\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		5700	pF
C_{oss}			1980	pF
C_{rss}			940	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = \pm 5\text{V}, V_{DS} = 50\text{V}, I_D = 8\text{A}$ $R_G = 3.3\Omega$ (External)		45	ns
t_r			43	ns
$t_{d(off)}$			340	ns
t_f			70	ns
$Q_{g(on)}$	$V_{GS} = \pm 5\text{V}, V_{DS} = 50\text{V}, I_D = 8\text{A}$		225	nC
Q_{gs}			22	nC
Q_{gd}			126	nC
R_{thJC}			0.18	$^\circ\text{C}/\text{W}$
R_{thCS}		0.21		$^\circ\text{C}/\text{W}$

Safe-Operating-Area Specification

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
SOA	$V_{DS} = 100\text{V}, I_D = 4.2\text{A}, T_C = 75^\circ\text{C}, t_p = 5\text{s}$	420		W

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
V_{SD}	$I_F = 16\text{A}, V_{GS} = -10\text{V}$, Note 1		0.80	1.30 V
t_{rr}	$I_F = 8\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = -10\text{V}$		205	ns
I_{RM}			8.50	A
Q_{RM}			0.88	μC

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

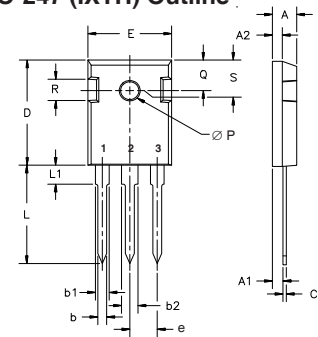
ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

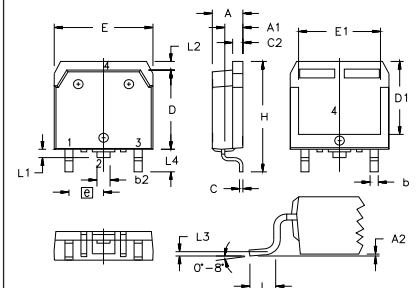
TO-247 (IXTH) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

TO-268 (IXTT) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

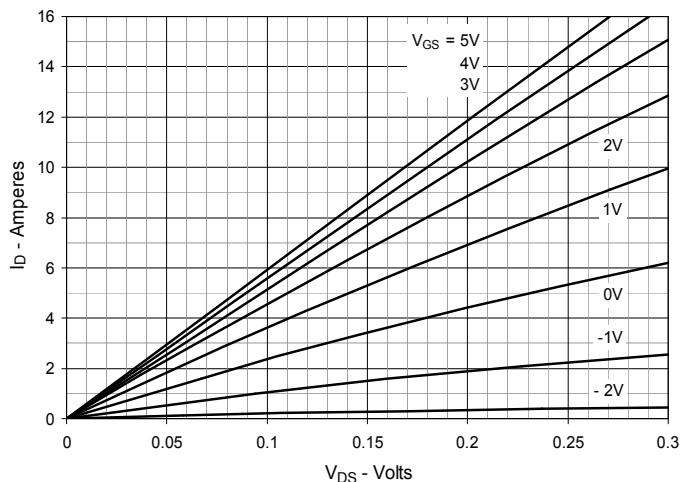


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

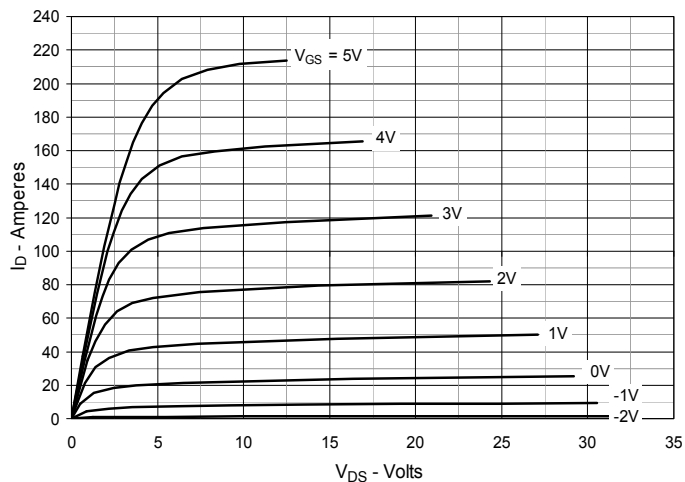


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

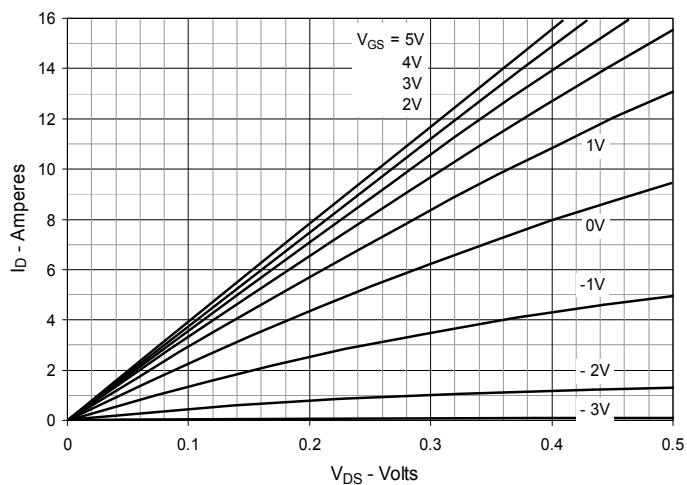


Fig. 4. Drain Current @ $T_J = 25^\circ\text{C}$

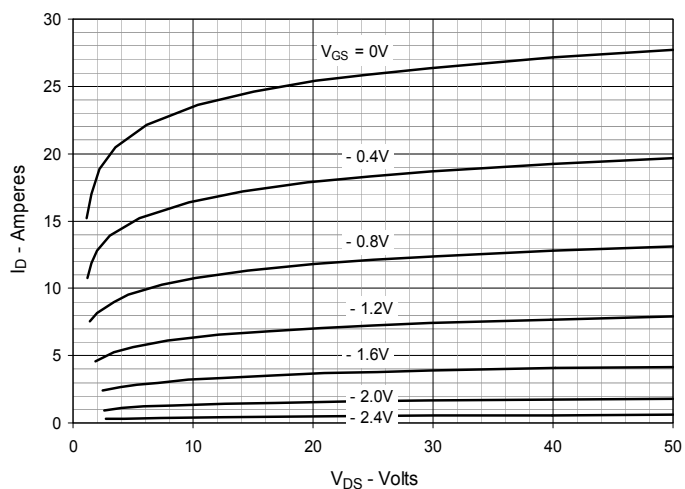


Fig. 5. Drain Current @ $T_J = 100^\circ\text{C}$

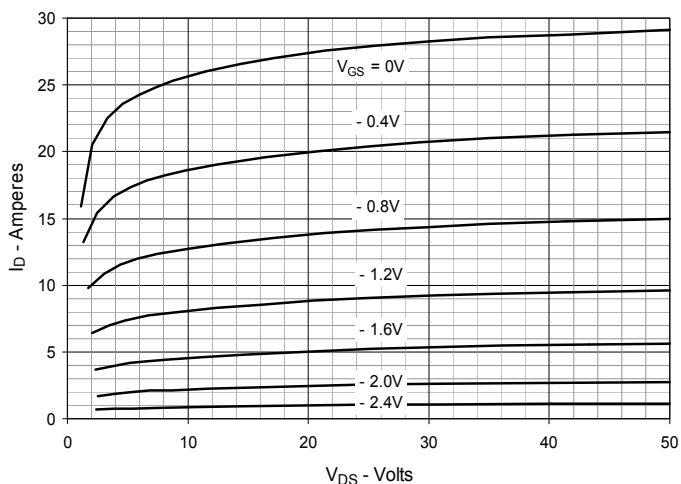


Fig. 6. Dynamic Resistance vs. Gate Voltage

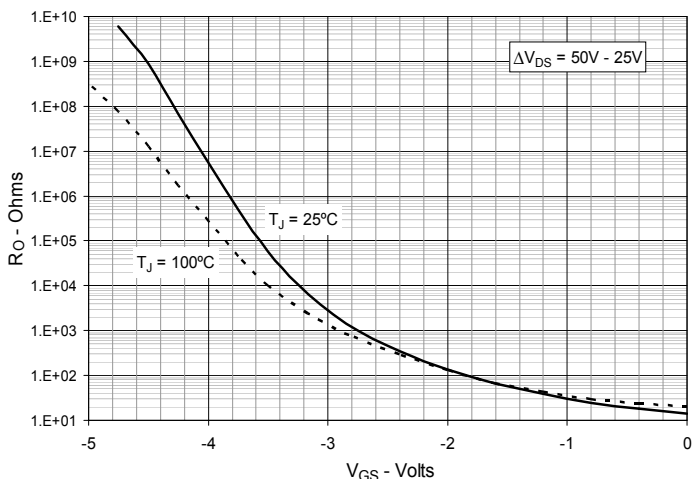


Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

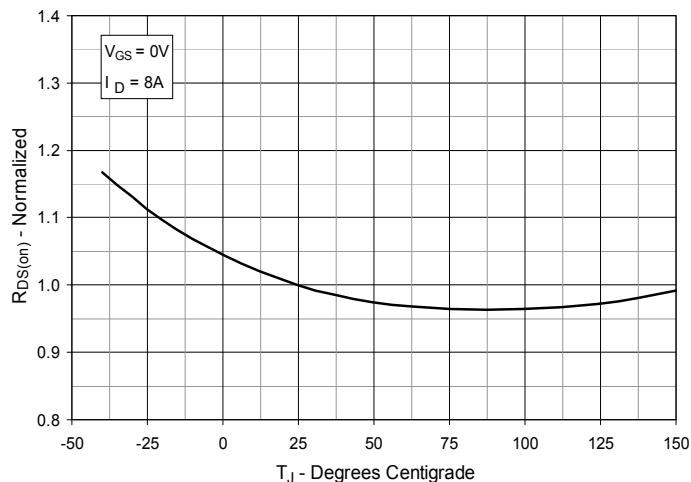


Fig. 8. $R_{DS(on)}$ Normalized to $I_D = 8A$ Value vs. Drain Current

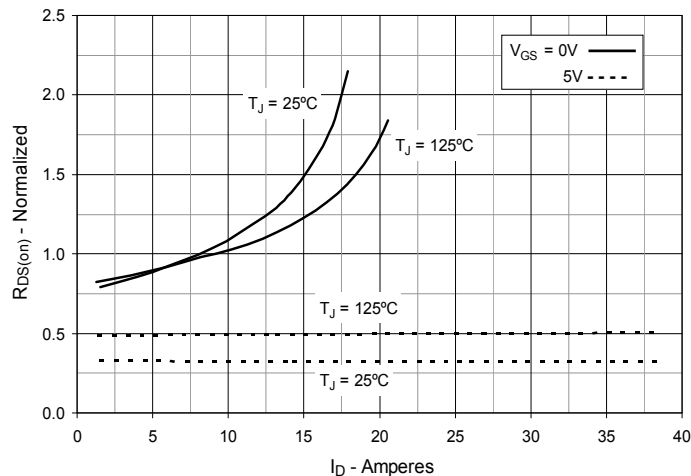


Fig. 9. Input Admittance

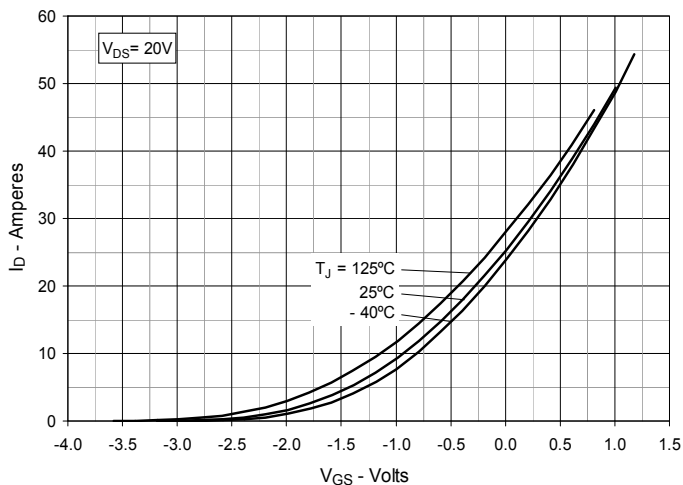


Fig. 10. Transconductance

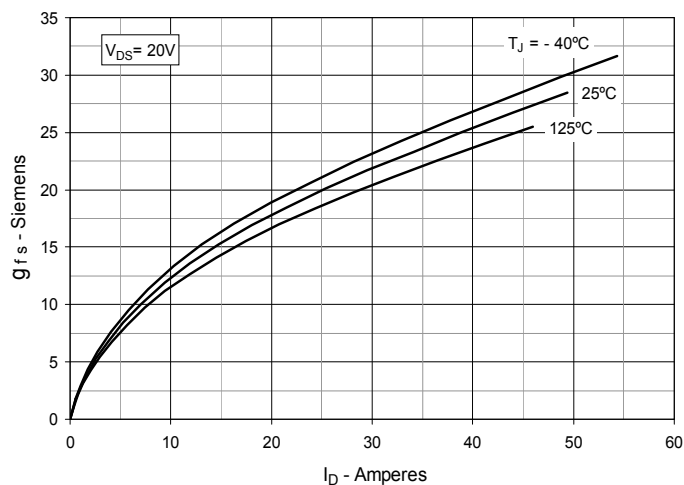


Fig. 11. Normalized Breakdown and Threshold Voltages vs. Junction Temperature

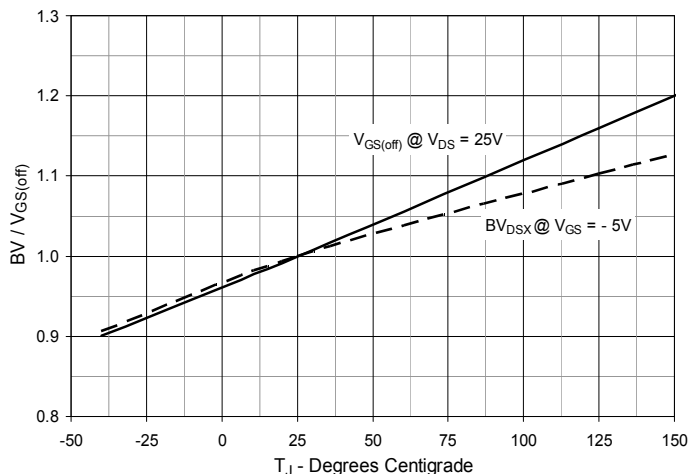


Fig. 12. Forward Voltage Drop of Intrinsic Diode

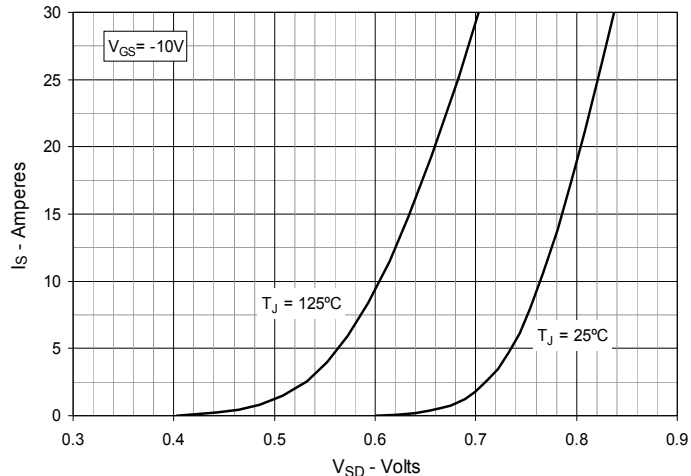


Fig. 13. Capacitance

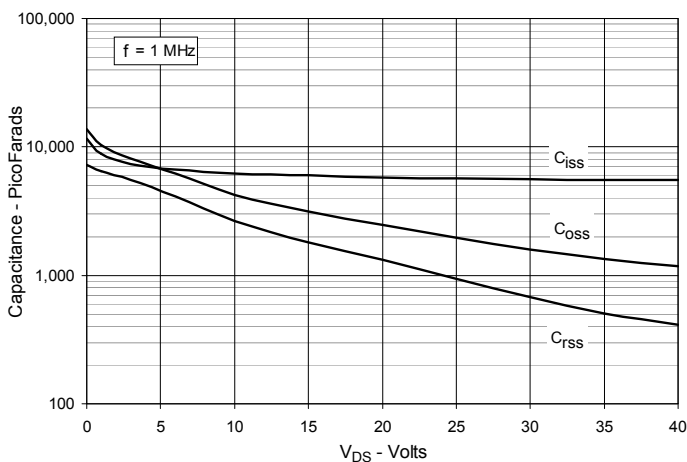
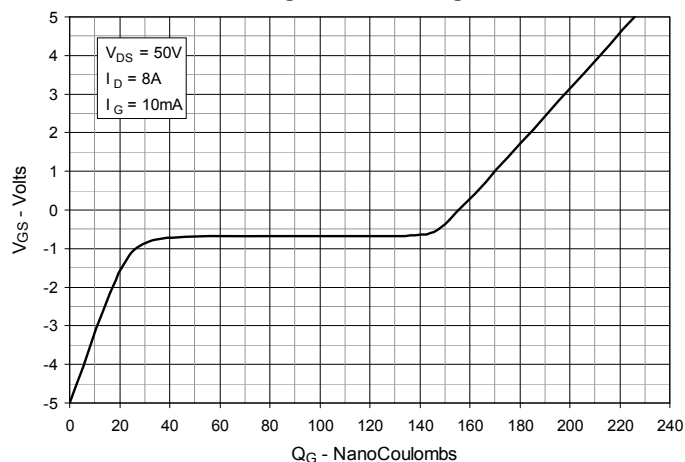
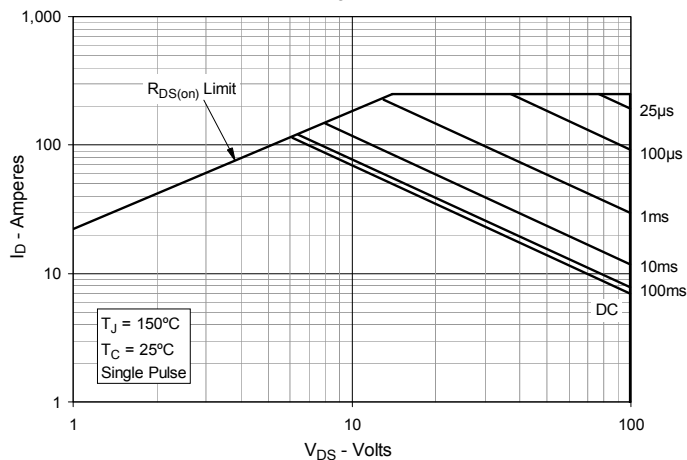


Fig. 14. Gate Charge



**Fig. 15. Forward-Bias Safe Operating Area
@ $T_C = 25^\circ\text{C}$**



**Fig. 16. Forward-Bias Safe Operating Area
@ $T_C = 75^\circ\text{C}$**

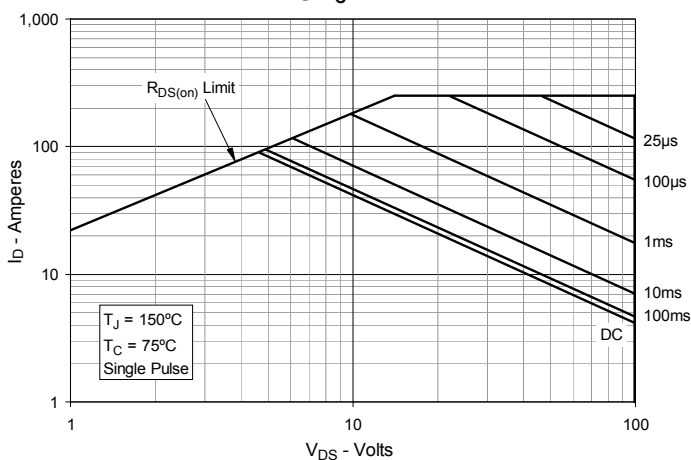


Fig. 17. Maximum Transient Thermal Impedance

